

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	§	
Chien-Chao Huang	§	Group Art Unit: Unknown
	§	
Serial No. Unknown	§	
	§	
Filed: Herewith	§	Examiner: Unknown
	§	
For: Method of Manufacturing A Microelectronic	§	
Device With Electrode Perturbing Sill	§	

**INFORMATION DISCLOSURE STATEMENT**

Commissioner For Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 CFR §1.56, and in accordance with the practice under 37 CFR §1.97 and §1.98, the Examiner's attention is directed to the documents listed on the enclosed modified Form PTO-1449. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited patents are listed in numerical order and are not in any order based on their pertinence.

The above-identified application is being after June 30, 2003. Therefore, pursuant to the waiver of the requirement under 37 CFR 1.98 (a)(2)(i) as stated in a Pre-OG Notice dated July 11, 2003, copies of only the foreign patent documents and non-patent literature listed on the enclosed modified Form PTO-1449 are attached.

This Information Disclosure Statement is being filed within three months of the United States filing date or before the mailing date of a first Office Action on the merits. No certification or fee is required (37 CFR §1.97(b)).

The Commissioner is hereby authorized to charge any additional fees which may be required or credit any overpayment to Deposit Account 08-1394.

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Respectfully submitted,



David M. O'Dell  
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R-72373.1

**Certificate of Mailing**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner For Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 4-15-04.

Bonnie Boyle  
Printed Name

Bonnie Boyle  
Signature

In place of PTO-1449 Form	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	
		Filing Date	Herewith
		Applicant(s)	Chien-Chao Huang
		Art Unit	
		Examiner Name	
SHEET	1	OF	1
		Attorney Docket Number	24061.150 (TSMC2003-0964)

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date <small>MM-DD-YYYY</small>	Name of Patentee or Applicant of Cited Document
	AA	6,583,000	06-24-2003	Hsu et al.
	AB	6,600,170	07-29-2003	Xiang

FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document <small>(Country Code - Number - Kind)</small>	Publication Date <small>MM-DD-YYYY</small>	Patentee or Applicant of Cited Document	Translation <small>Y/N</small>

OTHER PRIOR ART		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
	AC	Y. C. YEO et al., "Enhanced Performance in Sub-100 nm CMOSFETs using Strained Epitaxial Silicon-Germanium", IEDM Technical Digest, December 10-13, 2000, pgs. 753-756, IEEE.
	AD	C. R. SELVAKUMAR et al., "Sige-Channel NMOSFET by Germanium Implantation", IEEE Electron Device Letters, 1991, Vol/Issue 12/8 August, pages 444-446, IEEE.
	AE	Y. H. Wu et al., "High Temperature Formed Sige P-Mosfets With Good Device Characteristics", IEEE Electron Device Letters, 2000, Vol./Issue 21/7 pages 350-352, IEEE.
	AF	D. K. Nayak et al., "High-Mobility Strained-Si P-Mosefets, IEEE Transactions on Electron Device, 1996, Vol./Issue 43/10/Oct, pages 1709-1716, IEEE
	AG	Xiang Lu et al., "SiGe and SiGeC Surface Alloy Formation Using High-dose Implantation and Solid Phase Epitaxy", International Conference on Ion Implantation Technology, 1997, pages 686 - EOA, IEEE.

Examiner Signature		Date Considered	
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.